Ordering number : ENN6800

Diffused Junction Type Silicon Diode

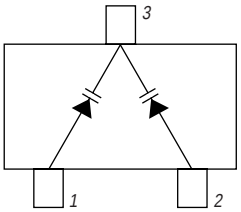
SVC236

Varactor Diode for FM Receiver Electronic Tuning Use

Features

- Low voltage (6.5V).
- Twin type varactor diode with good large-signal characteristics for FM receiver electronic tuning use.
- Very small package permits SVC236-applied sets to be compact and slim.
- Can be also provieded in tape reel package and automatic insertion is supported.
- High capacitance ratio (V_R=1.0 to 6.5V).

Electrical Connection



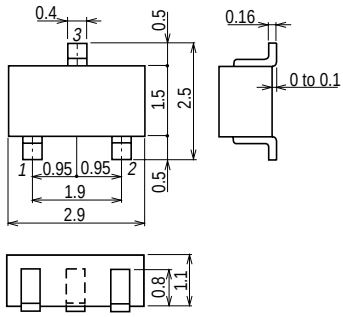
1 : Anode
2 : Anode
3 : Cathode

(Top view)

Package Dimensions

unit : mm
1169A

[SVC236]



1 : Anode
2 : Anode
3 : Cathode

SANYO : CP

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Reverse Voltage	V_R		16	V
Junction Temperature	Tj		125	°C
Storage Temperature	Tstg		-55 to +125	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Breakdown Voltage	$V_{(BR)R}$	I_R=10μA	16			V
Reverse Voltage	I_R	V_R=10V			50	nA
Interterminal Capacitance*	C1V	V_R=1.0V, f=1MHz*	92.07		102.12	pF
	C3.0V	V_R=3.0V, f=1MHz	35.14		41.98	pF
	C6.5V	V_R=6.5V, f=1MHz	14.44		16.84	pF
Quality Factor	Q	V_R=3.0V, f=100MHz	70			
Capacitance Ratio	CR	C1.0V / C6.5V	5.0			
Matching Tolerance	ΔCm	V_R=1.0V, 3.0, 6.5, f=1MHz (Cmax-Cmin) / CminX100			3.0	%

Note)* : Capacitance value per each diode. * : 1MHz signal : 20mVnms

Marking : ZV

SANYO Electric Co.,Ltd. Semiconductor Company
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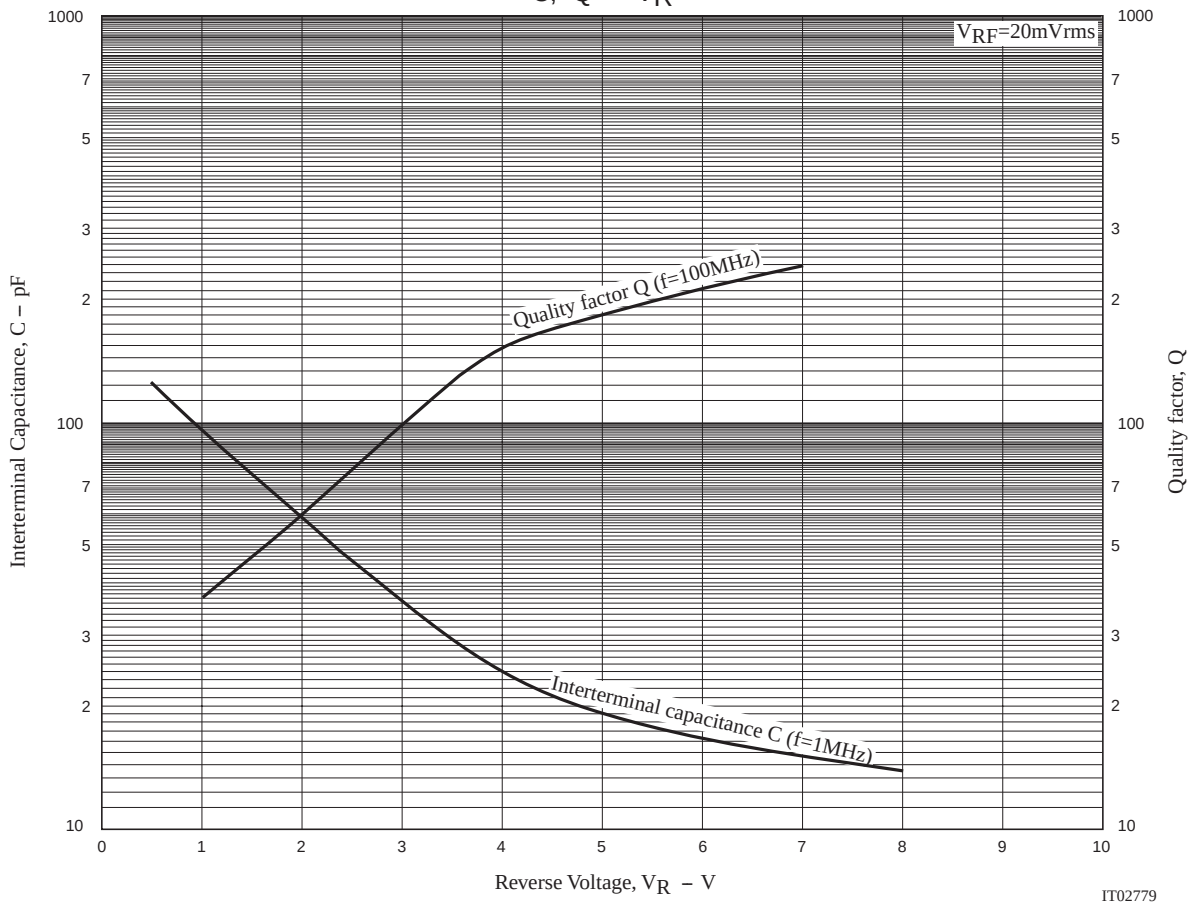
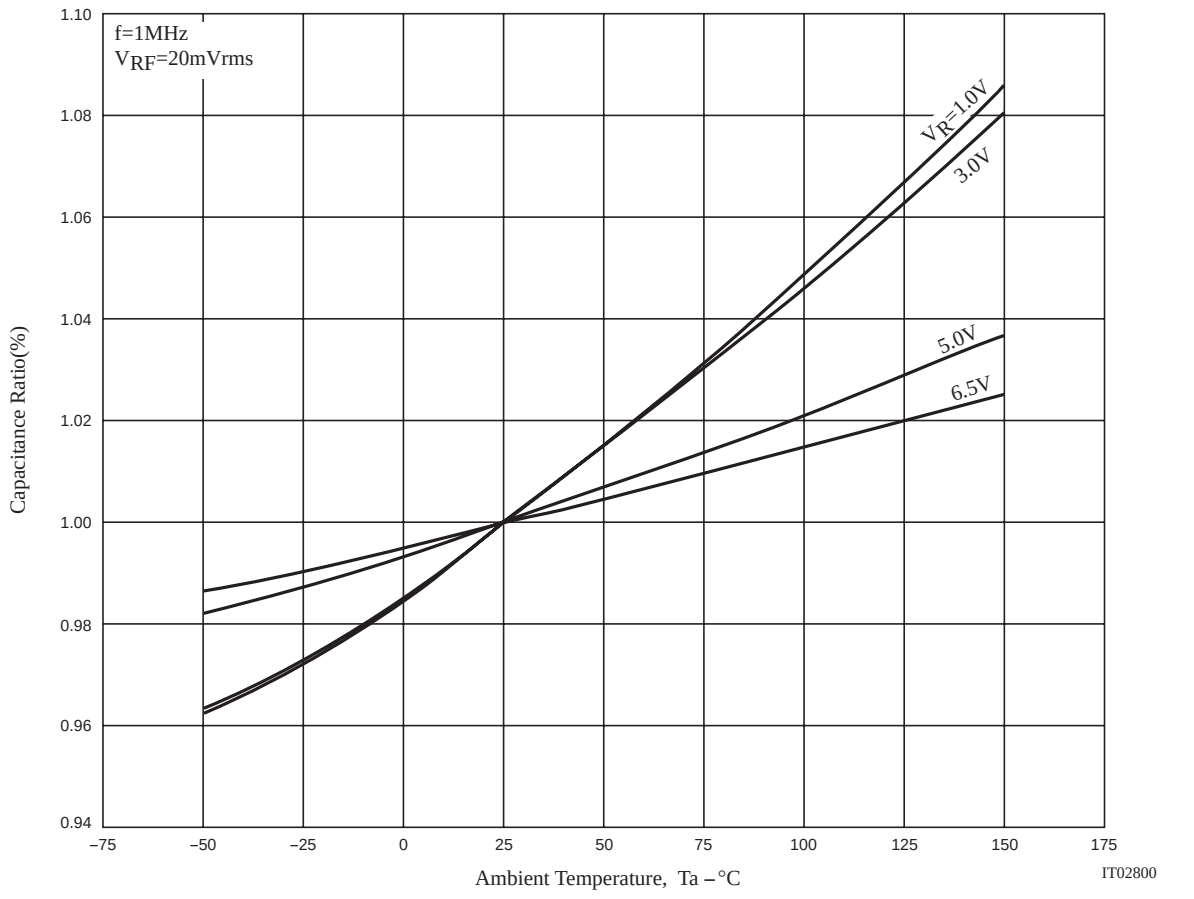
C, Q – V_R


V_{RF}=20mVrms
Quality factor Q (f=100MHz)
Interterminal capacitance C (f=1MHz)
Interterminal Capacitance, C – pF
Quality factor, Q
Reverse Voltage, V_R – V
IT02779

C – Ta


f=1MHz
V_{RF}=20mVrms
V_R=1.0V
3.0V
5.0V
6.5V
Capacitance Ratio(%)
Ambient Temperature, Ta – °C
IT02800